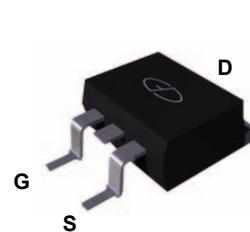
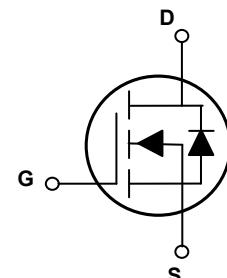


Main Product Characteristics

BV _{DSS}	80V
R _{DS(ON)}	4.2mΩ
I _D	130A



TO-263 (D²PAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFT08130 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V _{DS}	80	V
Gate-Source Voltage	V _{GS}	+20/-12	V
Drain Current-Continuous (T _C =25°C)	I _D	130	A
Drain Current-Continuous (T _C =100°C)		82	
Drain Current-Pulsed ¹	I _{DM}	520	A
Single Pulse Avalanche Energy ²	E _{AS}	451	mJ
Single Pulse Avalanche Current ²	I _{AS}	95	A
Power Dissipation (T _C =25°C)	P _D	184	W
Power Dissipation-Derate above 25°C		1.47	W/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62	°C/W
Thermal Resistance, Junction-to-Case	R _{θJC}	0.68	°C/W
Operating Junction Temperature Range	T _J	-55 To +150	°C
Storage Temperature Range	T _{STG}	-55 To +150	°C

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	80	-	-	V
Drain-Source Leakage Current	$I_{\text{DS}(\text{S})}$	$V_{\text{DS}}=80\text{V}, V_{\text{GS}}=0\text{V}, T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{\text{DS}}=64\text{V}, V_{\text{GS}}=0\text{V}, T_J=85^\circ\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	100	nA
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=20\text{A}$	-	3.5	4.2	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=250\mu\text{A}$	2	3	4	V
Forward Transconductance	g_{fs}	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=5\text{A}$	-	18	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{\text{DS}}=40\text{V}, I_{\text{D}}=70\text{A}$ $V_{\text{GS}}=10\text{V}$	-	95.5	143	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	23.5	35	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	32	48	
Turn-On Delay Time ^{3,4}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=40\text{V}, R_{\text{G}}=6\Omega$ $V_{\text{GS}}=10\text{V}, I_{\text{D}}=70\text{A}$	-	22	33	nS
Rise Time ^{3,4}	t_r		-	15	23	
Turn-Off Delay Time ^{3,4}	$t_{\text{d}(\text{off})}$		-	40	60	
Fall Time ^{3,4}	t_f		-	19	29	
Input Capacitance	C_{iss}	$V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	5510	8265	pF
Output Capacitance	C_{oss}		-	1200	1800	
Reverse Transfer Capacitance	C_{rss}		-	70	100	
Gate Resistance	R_g	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=0\text{V}, F=1\text{MHz}$	-	1.5	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_s	$V_G=V_D=0\text{V},$ Force Current	-	-	130	A
Pulsed Source Current	I_{SM}		-	-	260	A
Diode Forward Voltage	V_{SD}	$V_{\text{GS}}=0\text{V}, I_s=1\text{A}, T_J=25^\circ\text{C}$	-	-	1	V
Reverse Recovery Time	t_{rr}	$V_R=50\text{V}, I_s=10\text{A}$ $dI/dt=100\text{A}/\mu\text{s}$ $T_J=25^\circ\text{C}$	-	65	-	nS
Reverse Recovery Charge	Q_{rr}		-	125	-	nC

Note:

- Repetitive rating: Pulsed width limited by maximum junction temperature.
- $V_{\text{DD}}=25\text{V}, V_{\text{GS}}=10\text{V}, L=0.1\text{mH}, I_{\text{AS}}=95\text{A}, R_{\text{G}}=25\Omega$, starting $T_J=25^\circ\text{C}$.
- Pulse test: pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
- Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

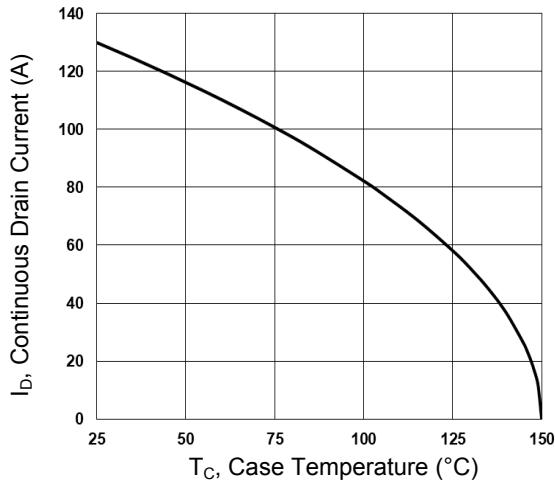


Figure 1. Continuous Drain Current vs. T_C

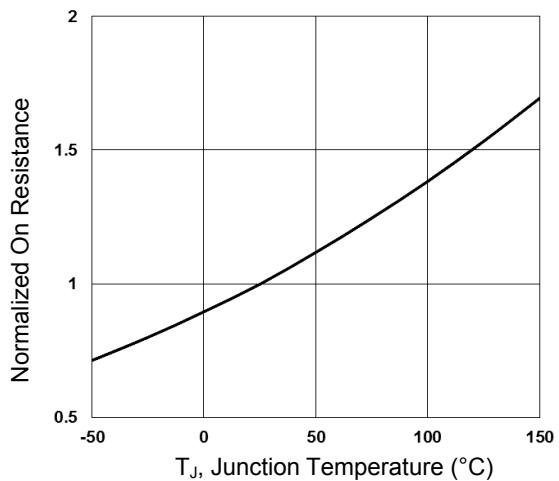


Figure 2. Normalized R_{DS(on)} vs. T_J

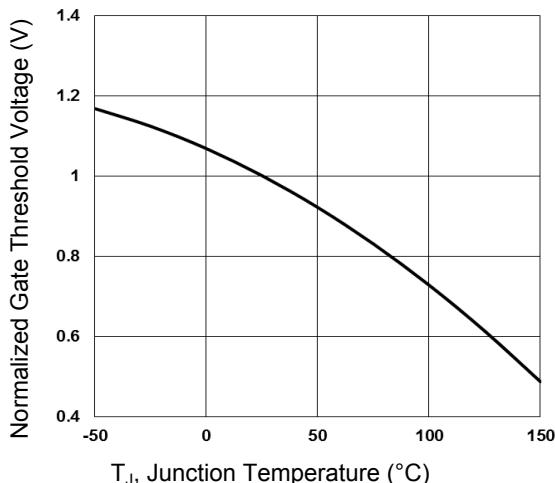


Figure 3. Normalized V_{th} vs. T_J

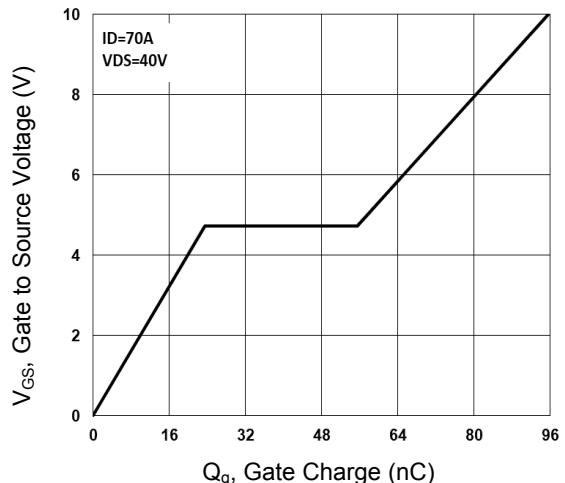


Figure 4. Gate Charge Characteristics

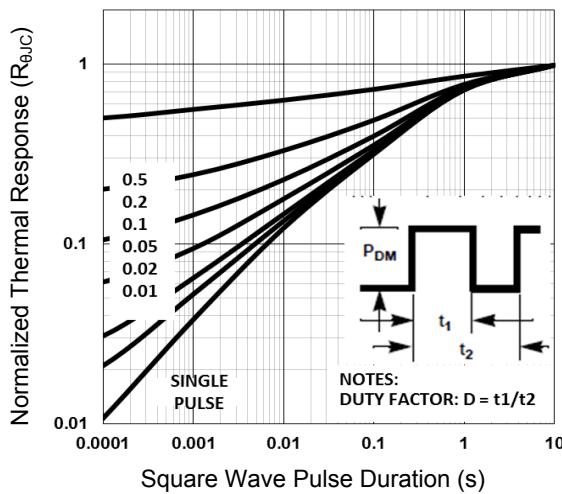


Figure 5. Normalized Transient Impedance

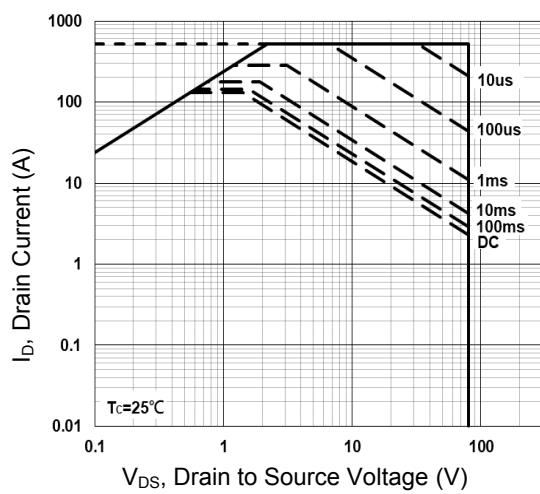


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

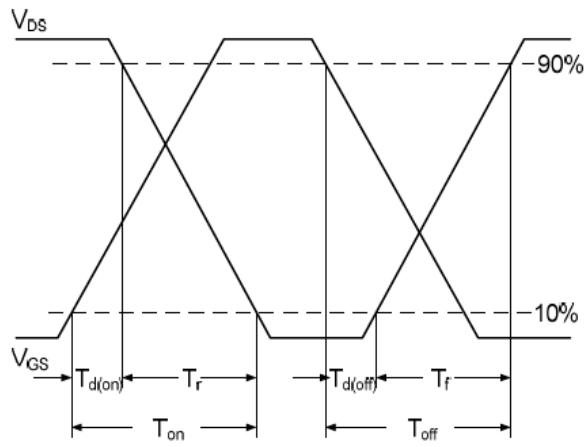


Figure 7. Switching Time Waveform

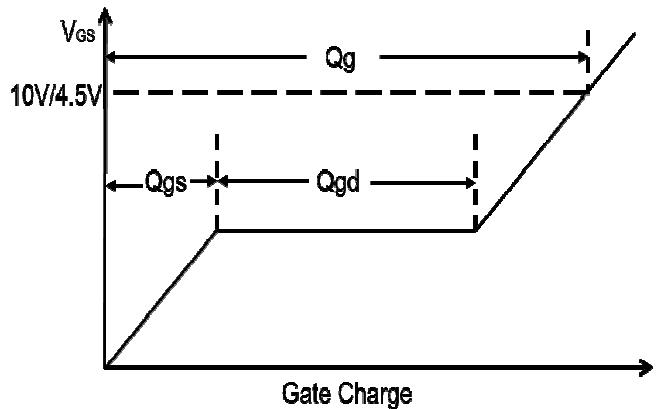
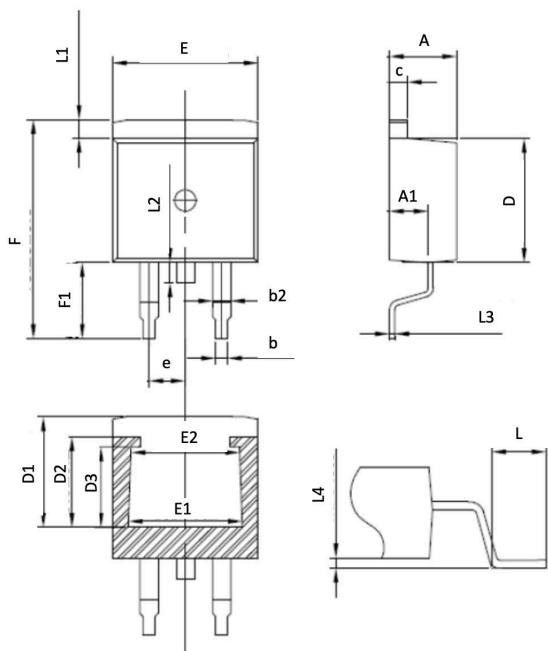


Figure 8. Gate Charge Waveform

Package Outline Dimensions (TO-263 (D²PAK))



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	4.250	4.650	0.167	0.183
A1	2.470	2.870	0.097	0.113
b	0.610	1.010	0.024	0.040
b2	1.070	1.470	0.042	0.058
c	1.170	1.370	0.046	0.054
D	8.650	9.250	0.341	0.364
D1	7.050	7.450	0.278	0.293
D2	5.700	6.100	0.224	0.240
D3	4.900	5.300	0.193	0.209
e	2.340	2.740	0.092	0.108
E	9.860	10.460	0.388	0.412
E1	7.800	8.200	0.307	0.323
E2	7.400	7.800	0.291	0.307
F	14.750	15.750	0.581	0.620
F1	4.740	5.340	0.187	0.210
L	1.985	2.585	0.078	0.102
L1	1.070	1.670	0.042	0.066
L2	1.300	1.700	0.051	0.067
L3	0.300	0.480	0.012	0.019
L4	-	0.300	-	0.012